

60 V, 10 A NPN high power bipolar transistor 27 May 2015

Product data sheet

### 1. General description

NPN high power bipolar transistor in a SOT669 (LFPAK56) Surface-Mounted Device (SMD) power plastic package.

PNP complement: PHPT60610PY

### 2. Features and benefits

- High thermal power dissipation capability
- High temperature applications up to 175 °C
- Reduced Printed Circuit Board (PCB) requirements comparing to transistors in DPAK
- High energy efficiency due to less heat generation
- AEC-Q101 qualified.

### 3. Applications

- Power management
- Load switch
- Linear mode voltage regulator
- Backlighting applications
- Motor drive
- Relay replacement

### 4. Quick reference data

Table 1. Quick reference data							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-	60	V
I <sub>C</sub>	collector current			-	-	10	А
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-	20	А
R <sub>CEsat</sub>	collector-emitter saturation resistance	$\begin{split} I_C &= 10 \text{ A};  I_B = 1 \text{ A}; \text{ pulsed};  t_p \leq 300  \mu\text{s}; \\ \delta &\leq 0.02  ;  T_{amb} = 25 ^\circ\text{C} \end{split}$		-	25	36	mΩ



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# 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E	emitter	mb	C
2	Е	emitter		в
3	E emitter	q	- M	
4	В	base		E sym123
mb	С	collector	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	571125

# 6. Ordering information

Table 3.       Ordering information						
Type number	Package					
	Name	Description	Version			
PHPT60610NY	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669			

# 7. Marking

Table 4. Marking codes	
Type number	Marking code
PHPT60610NY	0610NAB

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### 8. Limiting values

#### Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	60	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	60	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	7	V
I <sub>C</sub>	collector current			-	10	А
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	20	А
I <sub>B</sub>	base current			-	1.5	А
I <sub>BM</sub>	peak base current	single pulse; t <sub>p</sub> ≤ 1 ms		-	2	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	1.5	W
			[2]	-	3.7	W
			[3]	-	5	W
			[4]	-	25	W
Tj	junction temperature			-	175	°C
T <sub>amb</sub>	ambient temperature			-55	175	°C
T <sub>stg</sub>	storage temperature			-65	175	°C

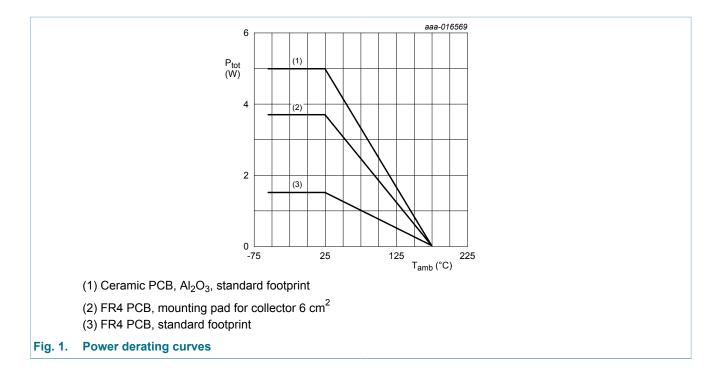
[1] Device mounted on an FR4 Printed-Circuit Board (PCB); single-sided copper; tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB; single-sided copper; tin-plated and mounting pad for collector 6 cm<sup>2</sup>.

[3] Device mounted on a ceramic PCB;  $AI_2O_3$ , standard footprint.

[4] Power dissipation from junction to mounting base.

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### 9. Thermal characteristics

Table 6.       Thermal characteristics							
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
R <sub>th(j-a)</sub> thermal resistance from junction to ambient		in free air	[1]	-	-	100	K/W
	-		[2]	-	-	41	K/W
	ambient		[3]	-	-	30	K/W
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base			-	-	6	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

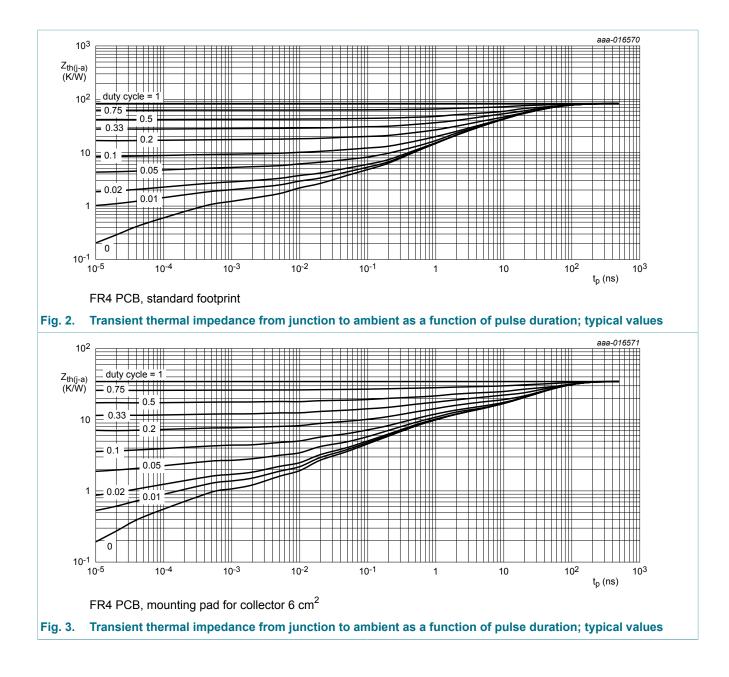
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for collector 6 cm<sup>2</sup>.

[3] Device mounted on a ceramic Printed-Circuit Board (PCB), Al<sub>2</sub>O<sub>3</sub>, standard footprint.

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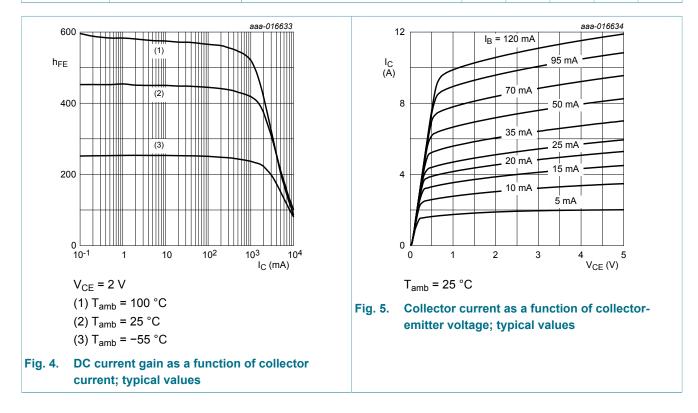
## **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	$V_{CB}$ = 48 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
	current	V <sub>CB</sub> = 48 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	50	μA
I <sub>CES</sub>	collector-emitter cut-off current	$V_{CE}$ = 48 V; $V_{BE}$ = 0 V; $T_{amb}$ = 25 °C	-	-	100	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB}$ = 7 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = 2 V; I <sub>C</sub> = 500 mA; T <sub>amb</sub> = 25 °C	240	410	-	
		$V_{CE} = 2 \text{ V; } I_C = 1 \text{ A; } t_p \le 300  \mu\text{s;}$ $\delta \le 0.02 \text{ ; } T_{amb} = 25 ^\circ\text{C}$	210	400	-	
		$V_{CE} = 2 \text{ V; } I_C = 5 \text{ A; } t_p \le 300  \mu\text{s;}$ $\delta \le 0.02 \text{ ; } T_{amb} = 25 ^\circ\text{C}$	100	200	-	
		$\label{eq:Vce} \begin{split} &V_{CE} \texttt{= 2 V; } I_{C} \texttt{= 10 A; } t_{p} \texttt{\le 300 \mu s;} \\ &\delta \texttt{\le 0.02 }; \; T_{amb} \texttt{= 25 °C; pulsed} \end{split}$	50	100	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$\begin{split} I_C = 1 \text{ A}; \ I_B = 50 \text{ mA}; \ t_p \leq 300  \mu\text{s}; \\ \delta \leq 0.02 \ ; \ T_{amb} = 25 \ ^\circ\text{C}; \ \text{pulsed} \end{split}$	-	30	40	mV
		$\begin{split} &I_{C} = 5 \text{ A}; \ I_{B} = 500 \text{ mA}; \text{ pulsed}; \\ &t_{p} \leq 300  \mu\text{s}; \ \delta \leq 0.02 \ \ ; \ T_{amb} = 25 \ ^{\circ}\text{C} \end{split}$	-	115	160	mV
		$I_{C}$ = 10 A; $I_{B}$ = 1 A; pulsed; $t_{p} \le 300 \ \mu s$ ;	-	250	360	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$\delta \le 0.02$ ; T <sub>amb</sub> = 25 °C	-	25	36	mΩ
V <sub>BEsat</sub>	base-emitter saturation voltage	$\begin{split} I_{C} &= 1 \text{ A};  I_{B} = 50 \text{ mA}; \text{ pulsed}; \\ t_{p} &\leq 300  \mu\text{s};  \delta \leq 0.02  ;  T_{amb} = 25 ^{\circ}\text{C} \end{split}$	-	-	0.95	V
		$\begin{split} I_{C} &= 5 \text{ A};  I_{B} = 500 \text{ mA}; \text{ pulsed}; \\ t_{p} &\leq 300  \mu\text{s};  \overline{\delta} &\leq 0.02  ;  T_{amb} = 25 ^{\circ}\text{C} \end{split}$	-	-	1.2	V
		$\begin{split} I_C &= 10 \text{ A};  I_B = 1 \text{ A}; \text{ pulsed};  t_p \leq 300  \mu\text{s}; \\ \delta \leq 0.02  ;  T_{amb} = 25 ^\circ\text{C} \end{split}$	-	-	1.4	V
V <sub>BEon</sub>	base-emitter turn-on voltage	$V_{CE}$ = 2 V; I <sub>C</sub> = 500 mA; T <sub>amb</sub> = 25 °C	-	-	0.8	V
t <sub>d</sub>	delay time	V <sub>CC</sub> = 12.5 V; I <sub>C</sub> = 5 A; I <sub>Bon</sub> = 250 mA;	-	20	-	ns
r	rise time	I <sub>Boff</sub> = -250 mA; T <sub>amb</sub> = 25 °C	-	180	-	ns
t <sub>on</sub>	turn-on time	=	-	200	-	ns
s	storage time	=	-	340	-	ns
f	fall time	-	-	165	-	ns
t <sub>off</sub>	turn-off time	-	-	505	-	ns

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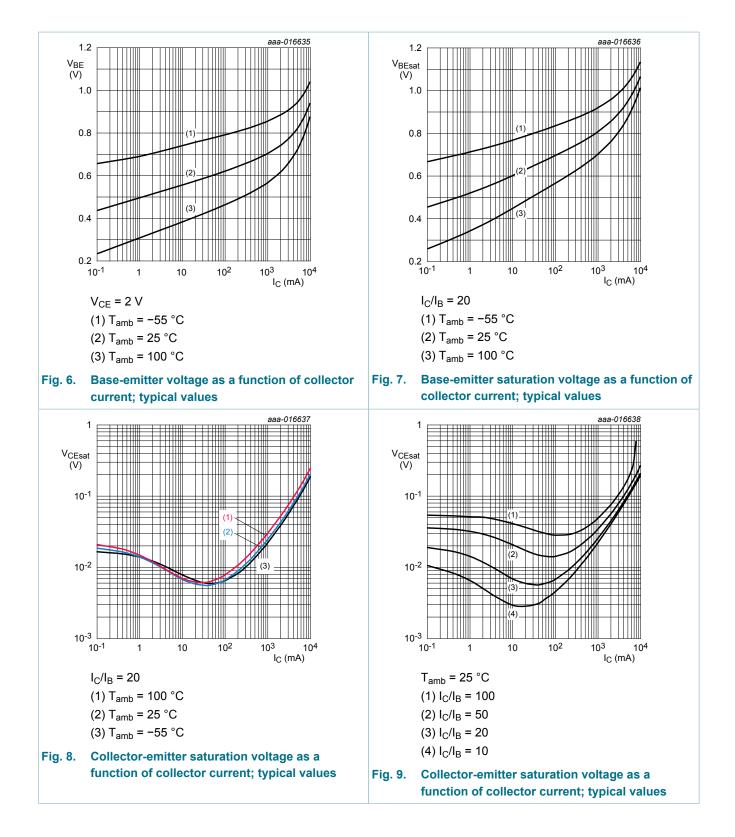
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f <sub>T</sub>	transition frequency	$V_{CE}$ = 10 V; I <sub>C</sub> = 500 mA; f = 100 MHz; T <sub>amb</sub> = 25 °C	-	140	-	MHz
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = 10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	50	-	pF



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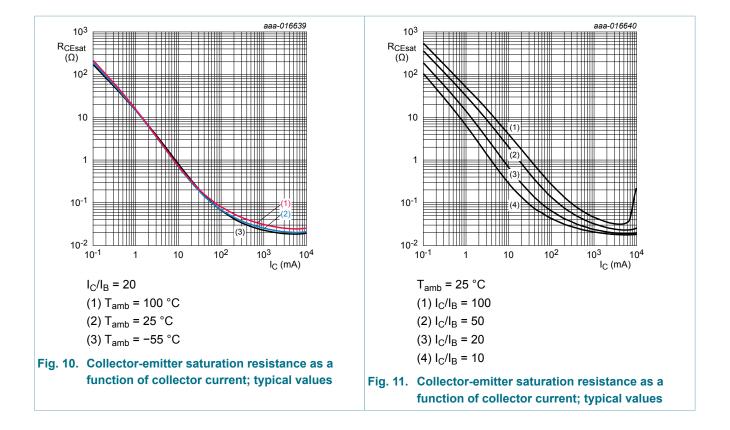
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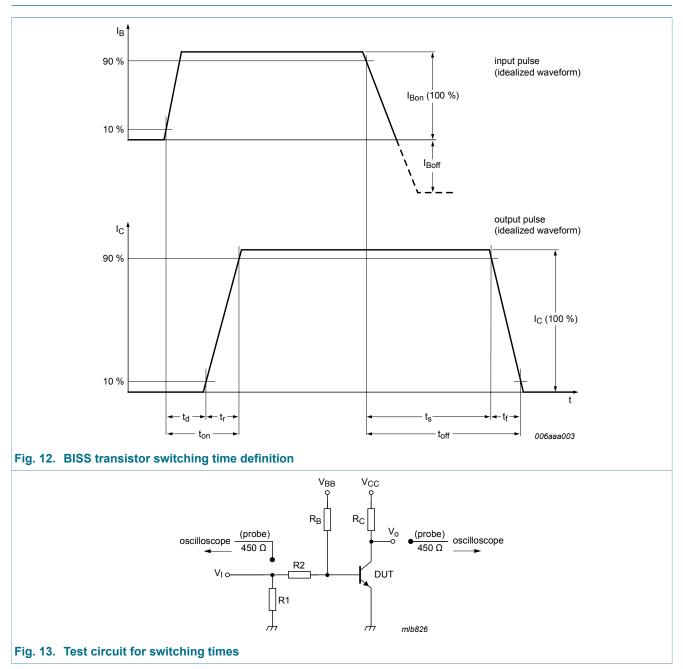
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### **11. Test information**

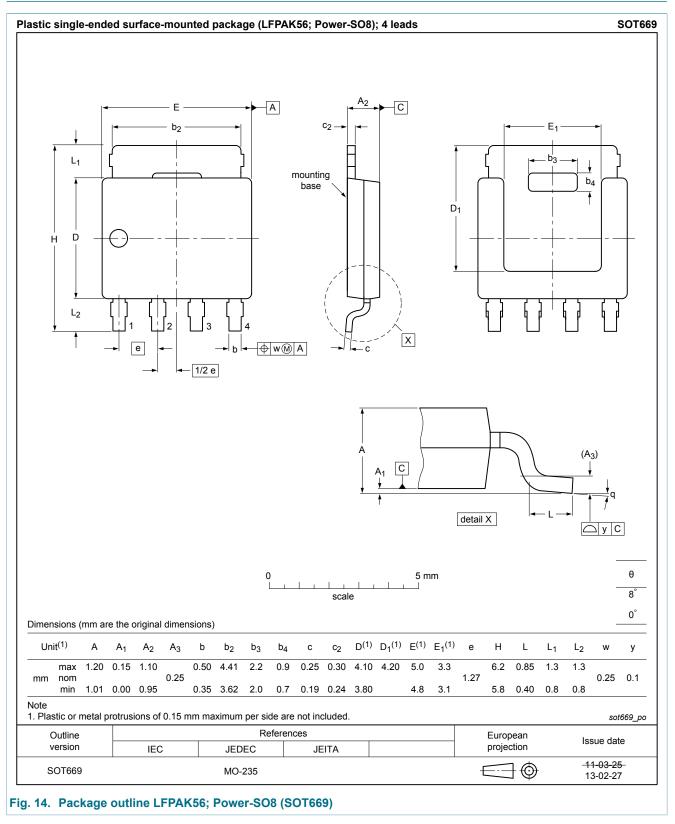
### **11.1 Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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### 12. Package outline

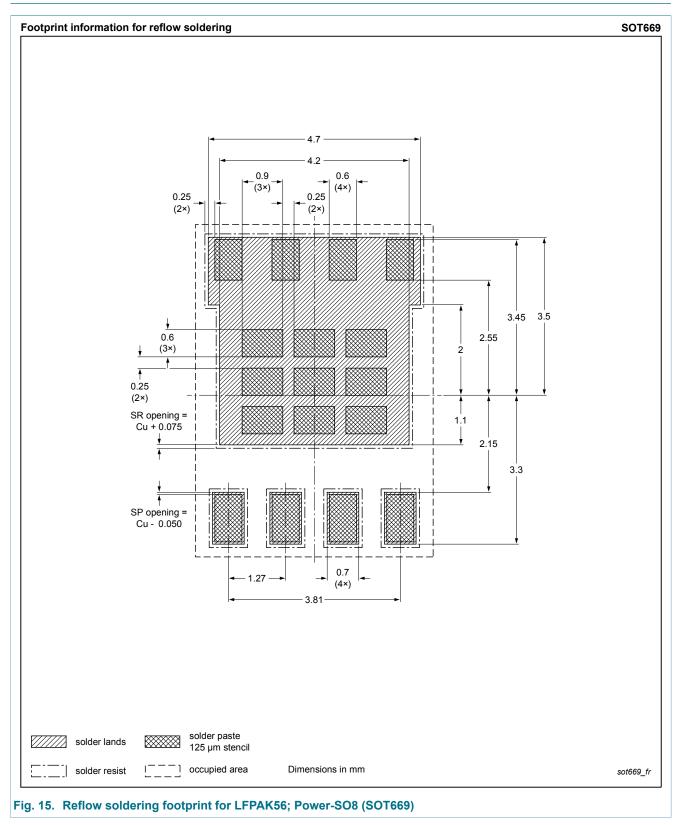


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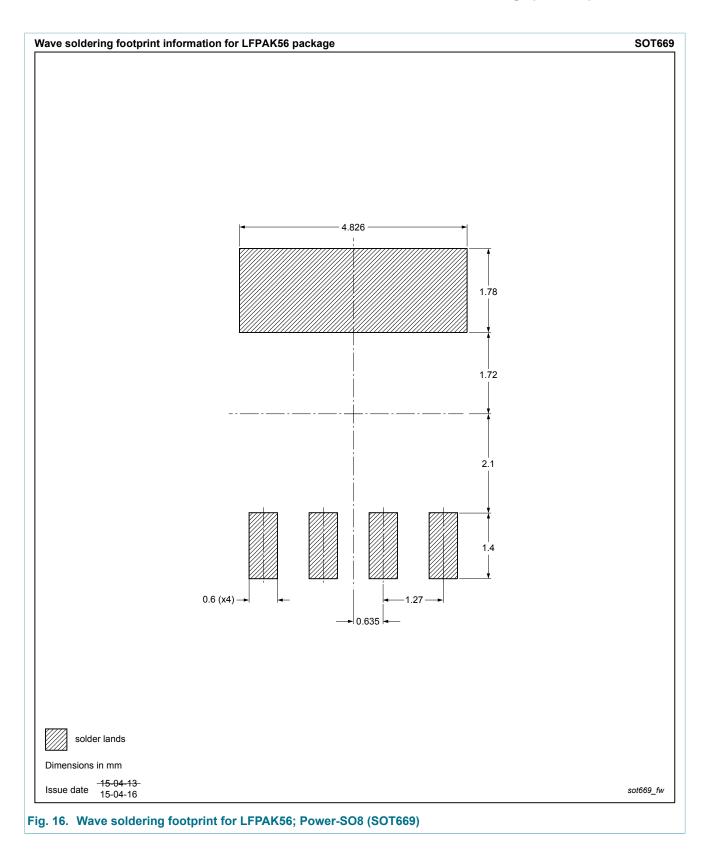
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### 13. Soldering



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### 60 V, 10 A NPN high power bipolar transistor

# 14. Revision history

Table 8. Revision history						
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PHPT60610NY v.1	20150527	Product data sheet	-	-		

#### 60 V, 10 A NPN high power bipolar transistor

### 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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